**Features:**

- n Isolated mounting base 3000V~
- n Pressure contact technology with Increased power cycling capability
- n Space and weight saving

**Typical Applications**

- n AC/DC Motor drives
- n Various rectifiers
- n DC supply for PWM inverter

$V_{RRM}, V_{DRM}$	Type & Outline	
2000V	MTx800-20-411F3	MFx800-20-411F3
2200V	MTx800-22-411F3	MFx800-22-411F3
2500V	MTx800-25-411F3	MFx800-25-411F3
2500V	MT800-25-411F3G	

MTx stands for any type of **MTC, MTA, MTK**  
 MFx stands for any type of **MFC, MFA, MFK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_J(^{\circ}\text{C})$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_{HS}=55^{\circ}\text{C}$	125			800	A
$I_{T(RMS)}$	RMS on-state current					1256	A
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	at $V_{DRM}$ at $V_{RRM}$	125			50	mA
$I_{TSM}$	Surge on-state current	$V_R=60\%V_{RRM}$ , $t=10\text{ms}$ half sine	125			16.0	kA
$I^2t$	$I^2t$ for fusing coordination		125			1280	$10^3\text{A}^2\text{s}$
$V_{TO}$	Threshold voltage		125			0.98	V
$r_T$	On-state slope resistance					0.35	mΩ
$V_{TM}$	Peak on-state voltage	$I_{TM}=2400\text{A}$	25			2.35	V
$dv/dt$	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			1000	V/μs
$di/dt$	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu\text{s}$ Repetitive	125			200	A/μs
$I_{GT}$	Gate trigger current	$V_A=12\text{V}$ , $I_A=1\text{A}$	25	30		200	mA
$V_{GT}$	Gate trigger voltage			0.8		3.0	V
$I_H$	Holding current			10		200	mA
$I_L$	Latching current					1000	mA
$V_{GD}$	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.20	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.050	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.024	$^{\circ}\text{C/W}$
$V_{iso}$	Isolation voltage	50Hz, R.M.S, $t=1\text{min}$ , $I_{iso}:1\text{mA(MAX)}$		3000			V
$F_m$	Terminal connection torque(M12)			12		16	N·m
	Mounting torque(M8)			10		12	N·m
$T_{vj}$	Junction temperature			-40		125	$^{\circ}\text{C}$
$T_{stg}$	Stored temperature			-40		125	$^{\circ}\text{C}$
$W_t$	Weight				3230		g
Outline	411F3						

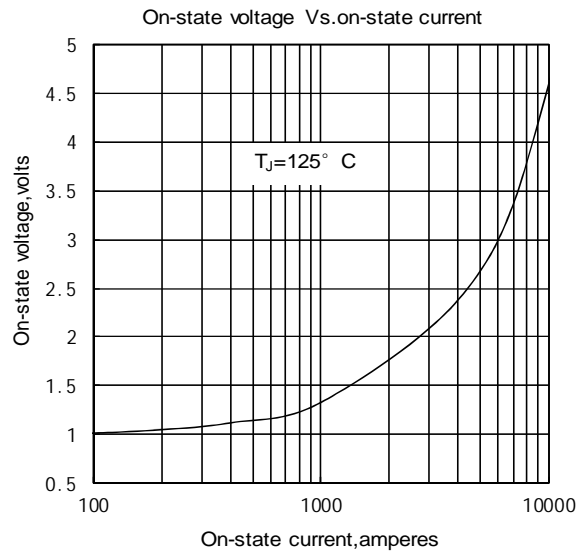


Fig.1

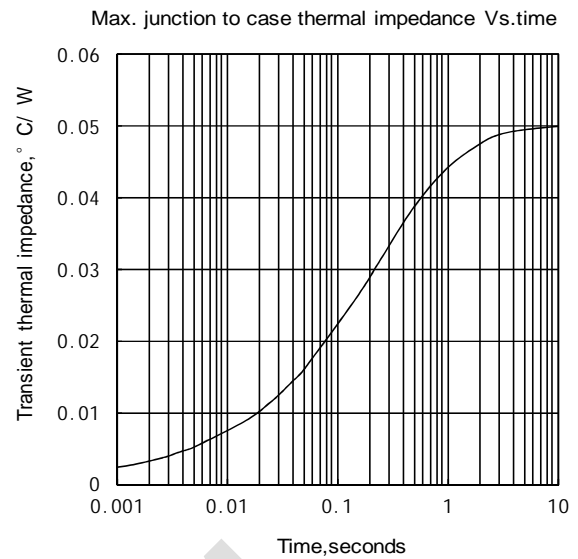


Fig.2

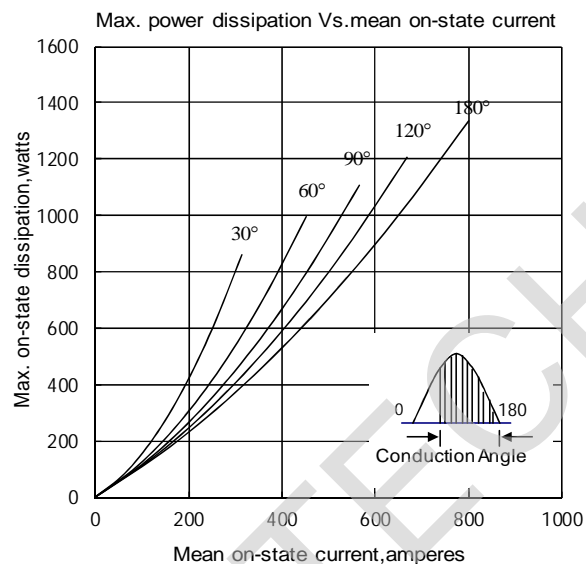


Fig.3

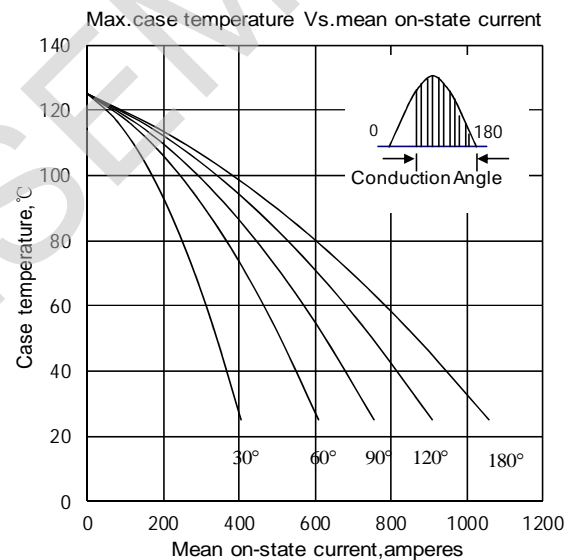


Fig.4

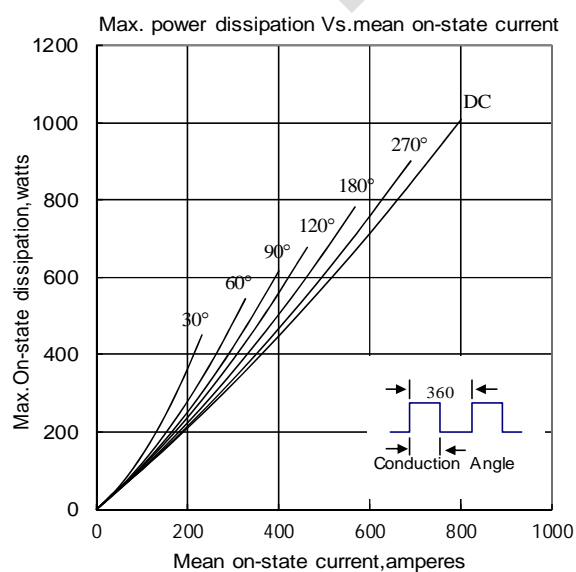


Fig.5

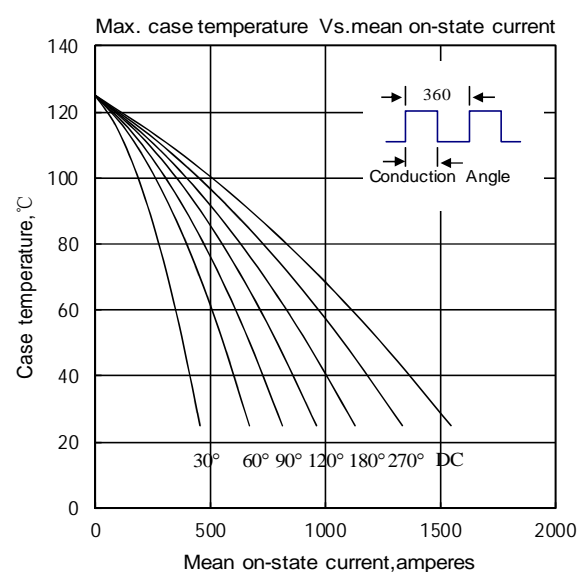


Fig.6

